EUROPEAN PATENT OFFICE

Patent Abstracts of Japan

PUBLICATION NUMBER : 05282868
PUBLICATION DATE : 29-10-93

APPLICATION DATE : 02-04-92
APPLICATION NUMBER : 04080862

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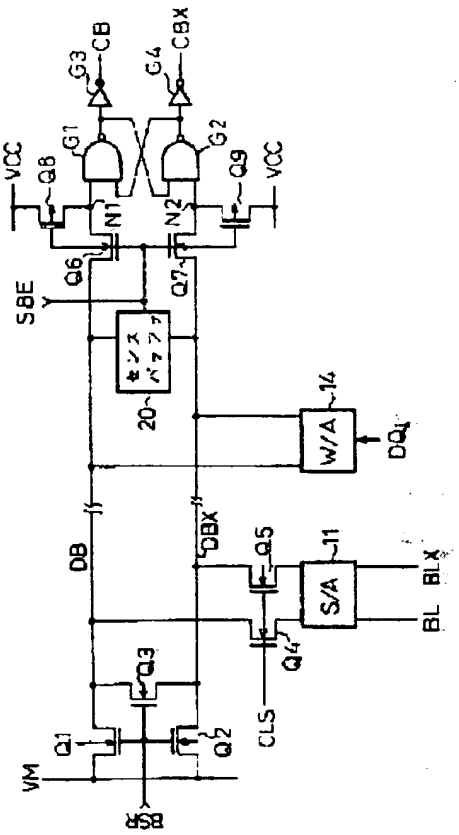
INT.CL. : G11C 11/409 H01L 27/108

TITLE : SEMICONDUCTOR STORAGE DEVICE



ABSTRACT : PURPOSE: To make high the speed of readout of data and to attain enlargement of an operation margin and reduction of power consumption by precharging a complementary data bus line at an intermediate potential substantially at the time when a pair of transistors are ON.

CONSTITUTION: Complementary data bus lines DB and DBX transmitting read data or write data and a power line VM having a substantially intermediate potential between a source voltage VCC of a high voltage and a source voltage VSS of a low potential are disposed. A pair of transistors Q1 and Q2 are connected between these complementary data bus lines DB and DBX and the power line VM. At the time when the paired transistors Q1 and Q2 are ON, the complementary data bus lines DB and DBX are precharged at the substantially intermediate potential in response to a reset signal BSR. Therefore, a differential voltage between the complementary data bus lines shows a level difference being twice as large as the one of a usual type, the speed of readout of data is made high, an operation margin 15 enlarged, a precharge level is lowered by half and power consumption can be reduced.